L Number	Hits	Search Text	DB	Time stamp
-	0	("ferroelectric adj memory").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:31
-	0	("insulat$ and substrate and contact adj hole and (burry buried)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:33
-	3514	ferroelectric adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:34
-	0	insulat$3 and substrate and contact adj hole and (burry and burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:24
-	0	insulat$3 and substrate and (burry and burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:36
-	337972	insulat$3 and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:36
-	1091	(ferroelectric adj memory) and (insulat$3 and substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:36
-	923	((ferroelectric adj memory) and (insulat$3 and substrate)) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:37
-	330	(((ferroelectric adj memory) and (insulat$3 and substrate)) and capacitor) and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:56
-	3	((((ferroelectric adj memory) and (insulat$3 and substrate)) and capacitor) and contact adj hole) and blocking adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:13
-	12043	kwon.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:53
-	12043	kwon-s.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:53
-	134	kwon-s-y.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 08:54
-	134	'kwon, s y'.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:22

-	2	6162649.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:23
-	2	6379977.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:23
-	2	6210979.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 09:24
-	43	insulat$3 and substrate and contact adj hole and (burry or burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:24
-	0	((438/3,253,254,238,396).CCLS.) and (insulat$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:25
-	1	((257/295,298,310,532).CCLS.) and (insulat$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:25
-	27	(((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole) and ((silicon adj oxynitride) or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:31
-	45	((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:40
-	54	(((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 17:02
-	124	((257/295,298,310,532).CCLS.) and buried near3 contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:41
-	2641	(257/295,298,310,532).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:43
-	4442	(257/295,296,298,310,532).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 16:05
-	5525	(438/3,253,254,238,396).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 12:46
-	2	5411911.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/08 16:05

–	29	(((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 09:25
–	2	6144052.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 10:39
–	2	6316803.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/09 10:39
–	150211	"12" and ((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 09:25
–	153281	((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 09:25
–	22	(((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:43
–	1	09/947378	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/03 15:37
–	17	"DRAM" and (((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:43
–	17	"DRAM" and capacitor and (((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:59
–	2040	(((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:28
–	1	("DRAM" and capacitor and (((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')) and (((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:54
–	488	"DRAM" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:55
–	370	("DRAM" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:55

–	4	(("DRAM" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))) and capacitor) and (((ferroelectric adj memory) and (insulat$3 and substrate)) and capacitor) and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:56
–	4	"FeRAM" and capacitor and (((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:00
–	4	("FeRAM" and capacitor and (((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')) not ((("DRAM" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))) and capacitor) and (((ferroelectric adj memory) and (insulat$3 and substrate)) and capacitor) and contact adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:01
–	886	"FeRam"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:01
–	10	"FeRam" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:02
–	2186	(((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:30
–	10	((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO")) and feram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:34
–	0	(((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO")) and feram) not ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:34
–	503	((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO")) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 10:35
–	378	(((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO")) and dram) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 15:23
–	28	((((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO")) and dram) and capacitor) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 14:30

-	29	((((((blocking adj layer) (etch adj stop)) with ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 14:30
-	2	("5891799").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/05 08:43
-	2	("6329680").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/05 09:19
-	4	(("6251726") or ("5976977")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/05 10:12
-	2	("6040596").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/05 10:12